

**Amendments to the Specification:**

**IN THE SPECIFICATION:**

Please replace paragraph [0048] as follows:

[0048] As shown in Fig. 9 (b), a small hole 58 (for example, having a diameter of about 20  $\mu\text{m}$ ) is formed in a semiconductor wafer 5. The small hole 58 has a diameter that is smaller than the through hole 4 described above with reference to Fig. 1, and is formed in the center of the through hole 4. The small hole 58 may be formed by using a laser (for example, YAG laser or ~~CO<sub>2</sub>~~ CO<sub>2</sub> laser). The laser beam can be irradiated while recognizing the position of the above-described recesses 54 and 56. The laser beam may be irradiated to one surface of the semiconductor wafer 5 to form the small hole 58, or the laser beam may be irradiated to both sides of the semiconductor wafer (successively or at the same time). Irradiation of the laser beam to the both sides causes less influences on the semiconductor wafer 5.